

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	38	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:31
S2	21	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45
S3	32	first near solution with (hf or "nh.sub.4f") and second near solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45
S4	1	defect same etch\$3 and evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S5	3124	defect same etch\$3 and evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S6	551	defect same etch\$3 and evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S7	13	defect same etch\$3 and evaluat\$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S8	4	defect same etch\$3 same evaluat\$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:46

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S9	103	defect same etch\$3 same evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:24
S10	26	crystal defect same etch\$3 same evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:42
S11	252	crystal defect and (secco or sertl or wright) with etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:43
S12	42	crystal defect same (secco or sertl or wright) with etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:45
S13	4	crystal defect same (secco or sertl or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S14	4	crystal defect and (secco or sertl or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
S15	4	crystal defect and (secco or sertl or wright) same etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
S16	1	crystal defect and evalut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54

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S17	0	crystal defect and evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
S18	2209	crystal defect and evaluat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
S19	16	crystal defect same evaluat\$3 same reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
S20	0	crystal defect same evaluat\$3 same reference wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:07
S21	1	crystal defect same evaluat\$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
S22	1	crystal defect and evaluat\$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
S23	4	crystal defect and evaluat\$3 and reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:12
S24	448	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:15

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S25	418	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S26	253	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S27	0	("crystaldefectandhfwithconcentrati on").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 09:03
S28	154	crystal defect and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:38
S29	39	crystal defect and evaluat\$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:03
S30	1	crystal defect and evaluat\$3 and hf with concentration and defect free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
S31	1	crystal defect and evaluat\$3 and hf with concentration and defect-free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
S32	39	crystal defect and evaluat\$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28

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S33	1	crystal defect and evaluat\$3 and defect free reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:06
S34	10	crystal defect and evaluat\$3 and defect free with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20
S35	0	crystal defect and evaluat\$3 and defect free with reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S36	1	crystal defect and evaluat\$3 and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S37	1	crystal defect and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S38	185	defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S39	8	defect free and reference image and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
S40	2	crystal defect and evaluat\$3 and defect free with reference and no defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20

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S41	11	crystal defect and evaluat\$3 and ((defect free) or (no defect)) with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:21
S42	47	crystal defect and (evaluat\$3 or detection) and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28
S43	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30
S44	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30
S45	36	defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
S46	0	defect and (evaluat\$3 or detection) same hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
S47	220	defect and (evaluat\$3 or detection) and hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
S48	12	defect and (evaluat\$3 or detection) same hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:08

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S49	58	crystal defect and (evaluat\$3 or detection) same hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:09
S50	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:10
S51	10	crystal defect same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:35
S52	152	ultrasonic wave same etch\$3 same clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S53	23	ultrasonic wave same etch\$3 same clean\$3 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S54	45	ultrasonic wave same etch\$3 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S55	13	ultrasonic wave same etch\$3 same known same clean\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:37
S56	2	("20050208322").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/22 10:18

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S57	167	crystal defect and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:38
S58	2	"20050208322"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 18:43
S59	10	etch\$3 same crystal defect and device pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 19:49
S60	257	etch\$3 same crystal defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 19:49
S61	44	selective\$2 with etch\$3 same crystal defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:07
S62	6	selective\$2 with etch\$3 same crystal defect same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S63	0	("257e21.53").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/08 20:27

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S64	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S65	61	S64 and etch\$3 and crystal with defect	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:30
S66	49	S64 and etch\$3 and crystal with defect and pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:30
S67	35	S64 and etch\$3 and crystal with defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S68	3	S64 and crystal with defect and etch\$3 same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/08 20:36
S69	2	"20050208322"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:12
S70	521	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:42

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S71	20	crystal defect same evaluat\$3 same reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
S72	451	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S73	269	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S74	45	defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:43
S75	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/11 03:43
S76	955	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S77	35	S76 and etch\$3 and crystal with defect and device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44

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S78	6	selective\$2 with etch\$3 same crystal defect same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:16
S79	15	defect same etch\$3 and evaluat\$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/06/11 03:44
S80	4	crystal defect same (secco or serti or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:17
S81	541	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:15
S82	462	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S83	273	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S84	981	(257/e21.53).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/22 22:16
S85	6	selective\$2 with etch\$3 same crystal defect same device with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:16

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S86	5	crystal defect same (secco or sertl or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:17
S87	46	defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:17
S88	46	S87	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:21
S89	10	SUGAMOTO-JUNJI.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:23
S90	80	TSUCHIYA-NORIIHIKO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:22
S91	171	USHIKU-YUKIHIRO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:23
S92	83	TANZAWA-KATSUJIRO .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/09/22 22:23